

INFORMATION DISCLOSURE CITATION IN AN APPLICATION			ATTY. DOCKET NO. 57810-084		SERIAL NO. Divisional of Appl No. 10/084,050	
(PTO-1449)			APPLICANT Nobuhiko HAYASHI, et al.			
			FILING DATE March 10, 2004		GROUP	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
De		US 6,015,979	1/18/2000	Sugiura et al.		
		US 6,051,849	4/18/2000	Davis et al.		
		US 6,503,769	01/07/2003	Nakamura et al.		
		US				
		US				
<b>FOREIGN PATENT DOCUMENTS</b>						
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De		2000-184989	6/18/2000			Yes Japan (w/ English Abstract)
		2000-269144	9/29/2000			No Japan (w/ English Abstract)
		2000-21789	1/21/2000			No Japan (w/ English Abstract)
		10-312871	11/24/1998			No Japan (w/ English Abstract)
<b>OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)</b>						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
De		S. Nakamura et al., "Long lifetime violet InGa/GaN/A1GaN-based semiconductor lasers", Journal of Oyo Denshi Bussai Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.				
		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.				
		Kevin Linthicum et al., "Pendeoepitaxy of gallium nitride thin films", Applied Physics Letter, Vol. 75, No. 2, July 12, 1999, pp. 196-198.				
		Isao Kidoguchi et al., "Air-bridged lateral epitaxial overgrowth of GaN thin films", Applied Physics Letter, Vol. 76, No. 25, June 19, 2000, pp. 3768-3770.				
EXAMINER De			DATE CONSIDERED 12/2005			

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		<b>APPLICANT</b> Nobuhiko HAYASHI, et al.				
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<i>De</i>		2000-184989	6/16/2000	—	—	Japan (w/ English Abstract)
		2000-269144	9/29/2000	—	—	Japan (w/ English Abstract)
		2000-21789	1/21/2000	—	—	Japan (w/ English Abstract)
		10-312971	11/24/1998	—	—	Japan (w/ English Abstract)
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